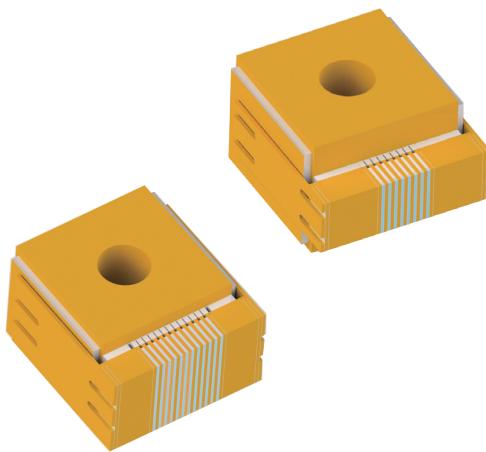


GS04 Series Diode laser

Vertical stacks



GS04 packaged diode laser array is RealLight's self-developed component in us-level applications, which features compact design, high power density, and small emitting size.

Key Features

- ◆ AuSn solder for packaging
- ◆ Compact design
- ◆ High peak power density
- ◆ High reliability

Applications

- Pumping source
Scientific research

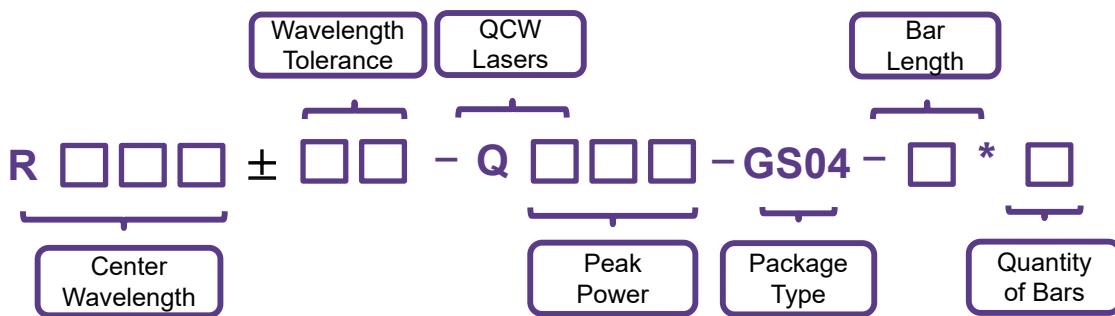
Technical Specifications

Optical Parameters		
Part Number	R808±3-Q640-GS04-3*8	R808±3-Q1200-GS04-5*12
Center Wavelength λ_c (nm)	808	
Wavelength Tolerance $\delta\lambda_c$ (nm)	± 3	
Output power of each Bar (W)	80	100
Bar Numbers	8	12
Spaces between Bars (mm)	~ 0.4	
Spectral Width (FWHM) (nm)	<5	
Slope Efficiency of each Bar (W/A)	>1.0	
Fast Axis Divergence Angle (FWHM) (°)	40	
Slow Axis Divergence Angle (FWHM) (°)	10	
Temperature Drift of Wavelength (nm/°C)	~ 0.3	
Electrical Parameters		
Conversion Efficiency (%)	>48	
Threshold Current I_{th} (A)	<12	<17
Operating Current I_{op} (A)	<85	<130
Operating Voltage V_{op} of each Bar (V)	<2	
Duty Cycle (%)	<0.8	
Pulse Width (μs)	<300	
Repetition Rate (Hz)	<30	
Environment Parameters		
Operating Temperature (°C)	0~45	
Storage Temperature (°C)	0~55	

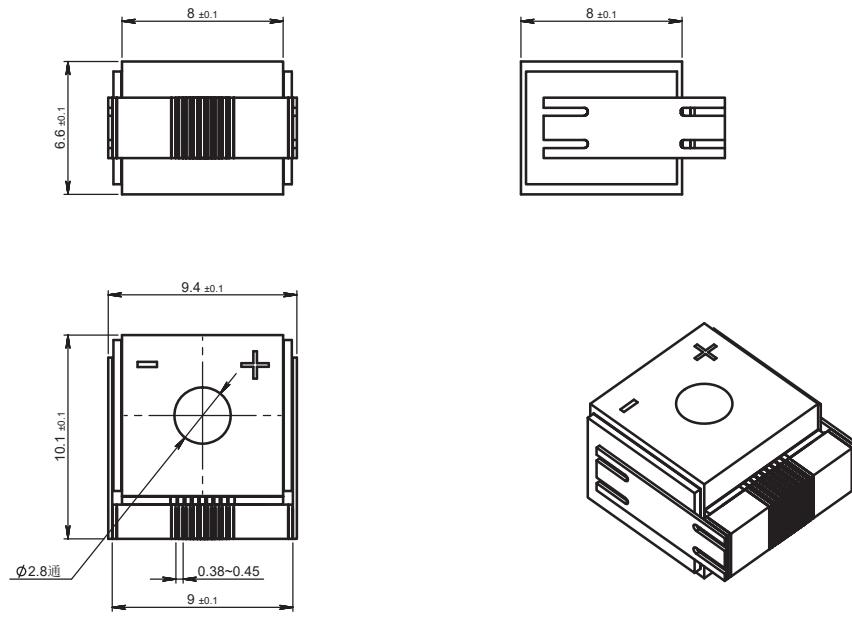
Notes:

- 1.Contact us if different parameters are required;
- 2.Do not operate it exceeding normal conditions, otherwise the life time will probably be decreased;
- 3.Make sure that there is no condensation in operating or storage environment;
- 4.All above parameters are measured in QCW mode.

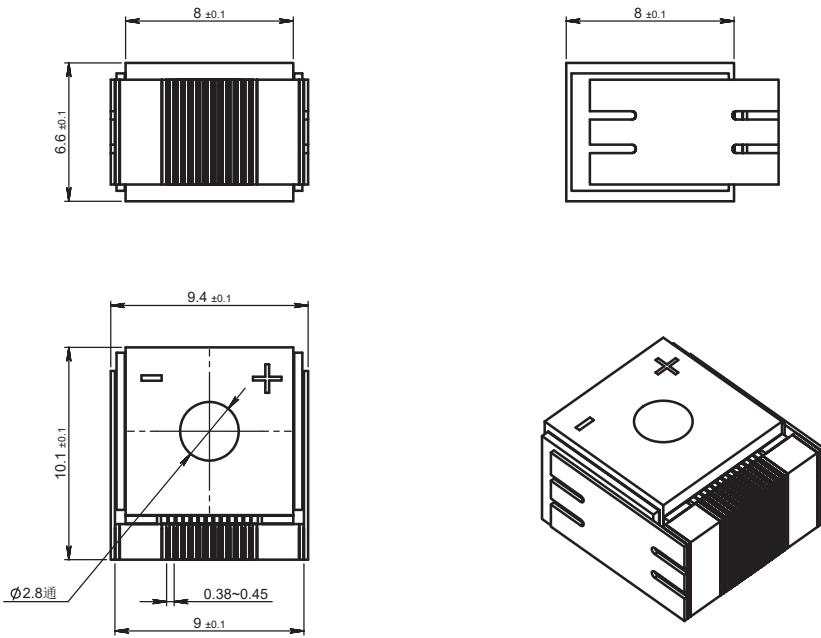
Part Numbering Schema



Mechanical Drawings (in mm)



R808±3-Q640-GS04-3*8



R808±3-Q1200-GS04-5*12

